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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>C mplete if Known</b>	
				Application Number	<del>Not Yet Assigned</del> 10/777 755
				Filing Date	February 13, 2004
				First Named Inventor	John T. Moore
				Art Unit	<del>Not Yet Assigned</del> 28/3
				Examiner Name	<del>Not Yet Assigned</del> Thompson
Sheet	1	of	8	Attorney Docket Number	M4065.0694/P694-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
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Examiner Initials*	Cite No. 1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> -Number <sup>5</sup> -Kind Code <sup>6</sup> (if known)				
CAT	BA	WO 97/48032	12/18/1997	Kozicki et al. **		
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Examiner Signature	<i>Craig A. Thompson</i>	Date Considered	8/27/04
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		Application Number	Not Yet Assigned 10/777755	
		Filing Date	February 13, 2004	
		First Named Inventor	John T. Moore	
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Sheet	2	8	Attorney Docket Number	M4065.0694/P694-A

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Sheet	4	8	Attorney Docket Number	M4065.0694/P694-A

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		Filing Date	February 13, 2004	
		First Named Inventor	John T. Moore	
		Group Art Unit	Not Yet Assigned 2813	
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		First Named Inventor	John T. Moore	
		Group Art Unit	Not Yet Assigned- 2813	
		Examiner Name	Not Yet Assigned	
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	CY5		
	CZ5		
	CA6		
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			Filing Date	February 13, 2004	
			First Named Inventor	John T. Moore	
			Art Unit	2811 2813	
			Examiner Name	Not Yet Assigned	
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		Number-Kind Code <sup>2</sup> (If known)			
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			Art Unit	2814-2813	
			Examiner Name	Not Yet Assigned	
Sheet	2	of	3	Attorney Docket Number	M4065.0694/P694-A

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